

N-Channel Enhancement-Mode MOSFET

DESIGNED FOR:

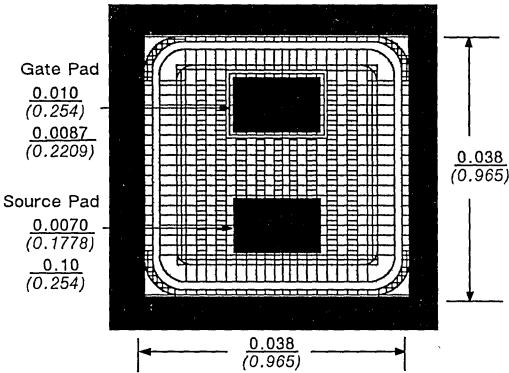
- Switching
- Amplification

FEATURES

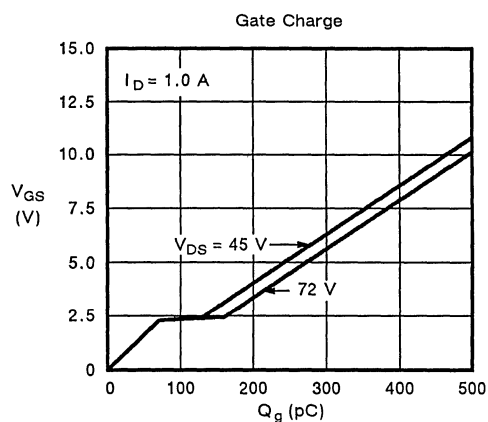
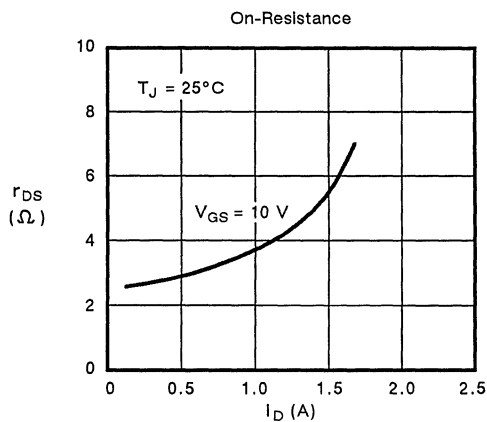
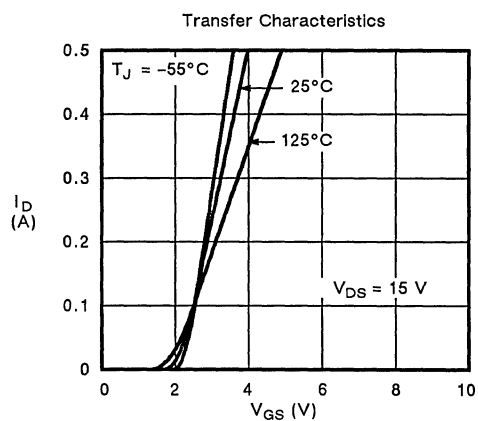
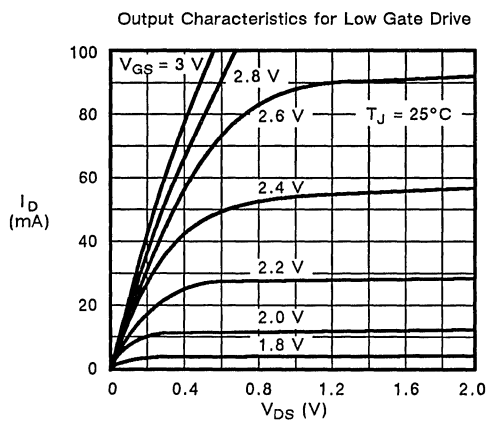
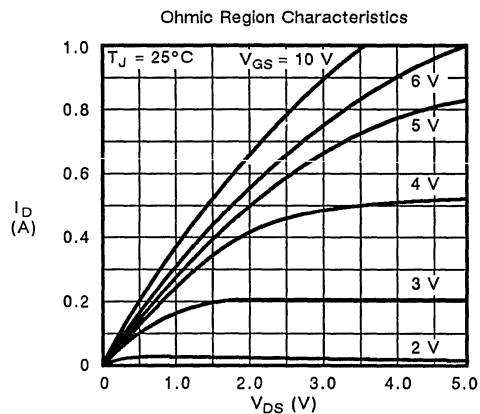
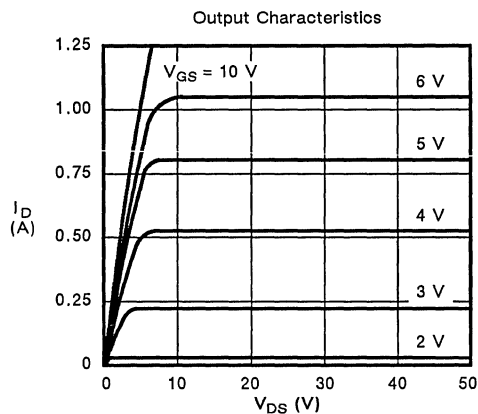
- Low $r_{DS(on)} < 4 \Omega$

TYPE	PACKAGE	DEVICE
Single	TO-205AD	• VN90AB 2N6661
	TO-92	• VN0808L
	TO-237	• VN0808M
	TO-220SD	• VN88AFD
	TO-220	• VN88AD
Quad	14-Pin Plastic	• VQ1006J
	14-Pin Dual-In-Line	• VQ1004P

GEOMETRY DIAGRAM

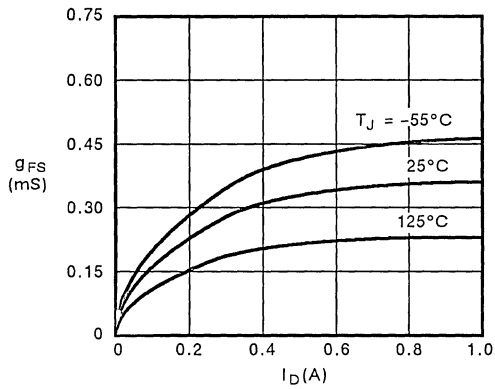


TYPICAL CHARACTERISTICS

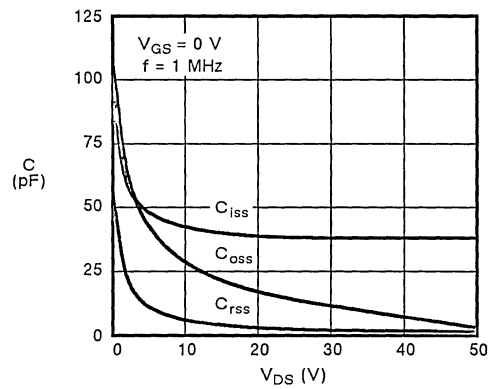


TYPICAL CHARACTERISTICS

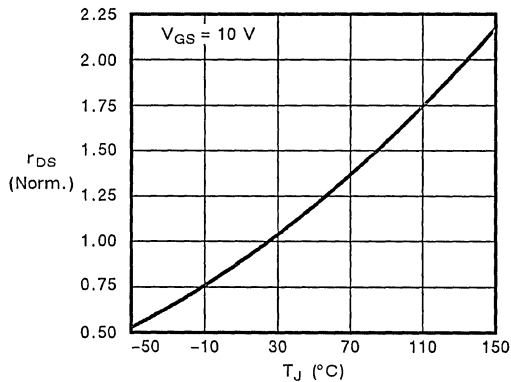
Transconductance



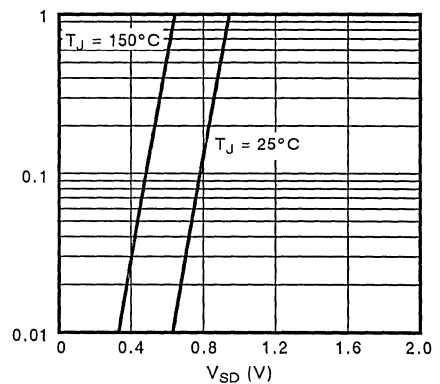
Capacitance



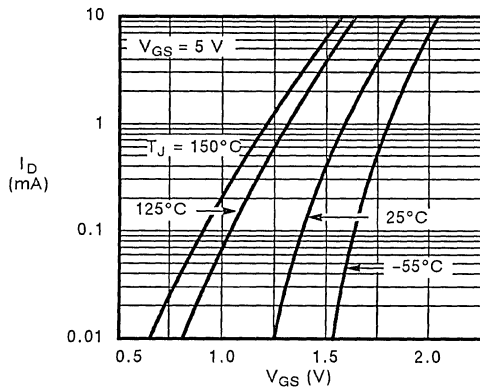
On-Resistance vs. Junction Temperature



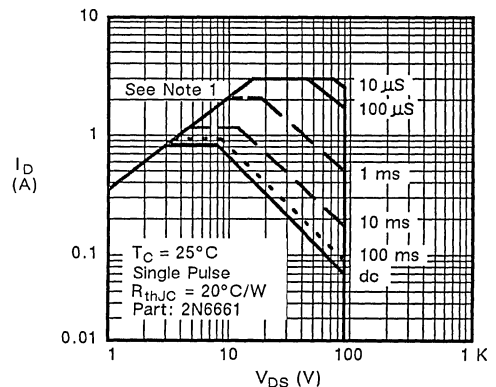
Source-Drain Diode Forward Voltage



Threshold Region

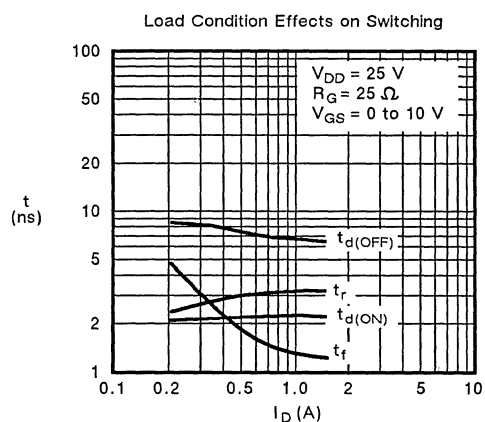
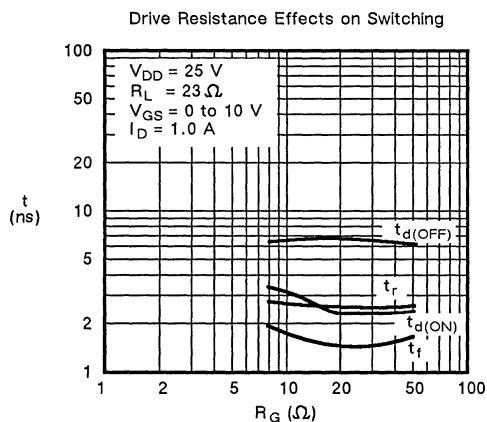
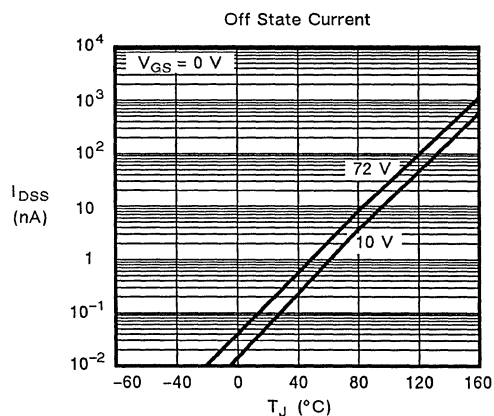
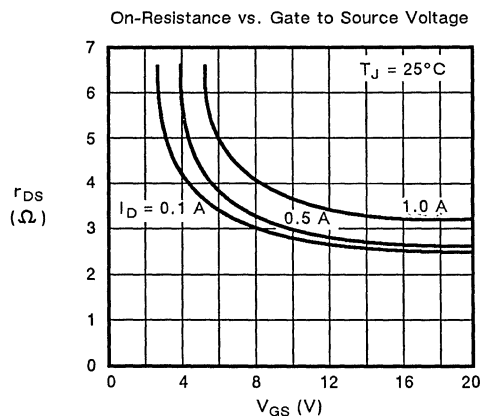
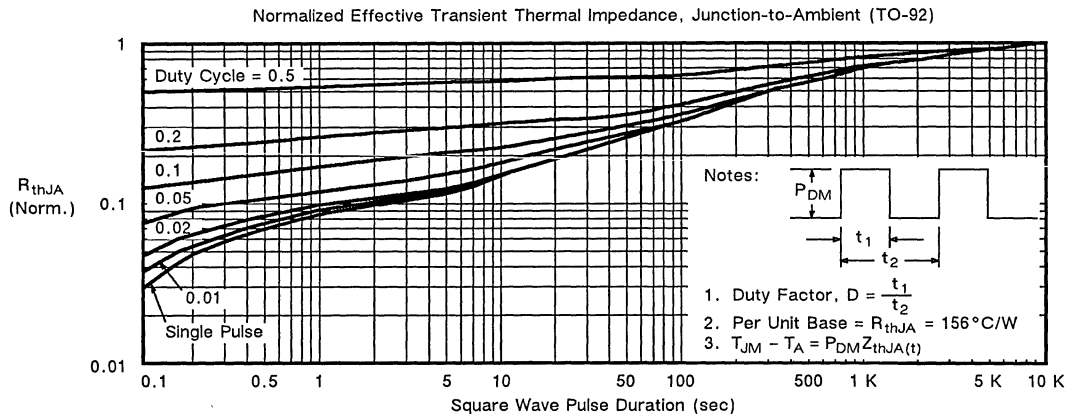


Safe Operating Area



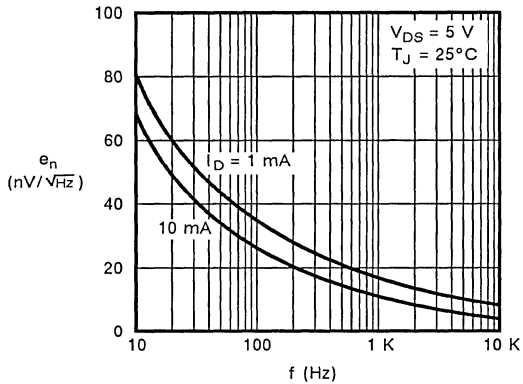
¹Operation in this area may be limited by $r_{DS(ON)}$

TYPICAL CHARACTERISTICS

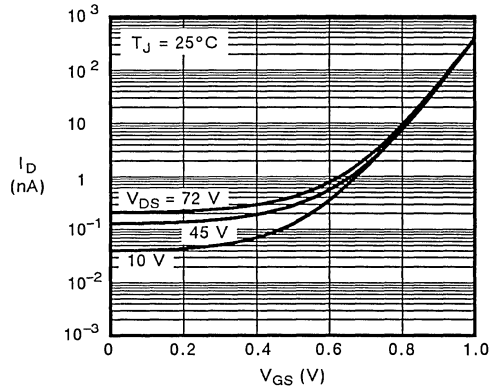


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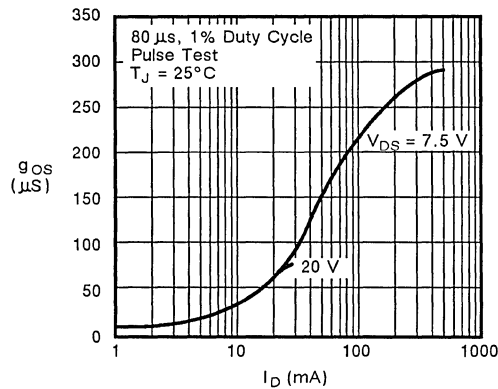
Equivalent Input Noise Voltage vs. Frequency



Body Drain Leakage Current



Output Conductance vs. Drain Current



Transient Thermal Response (TO-205AD)

